

IAP15 Rec'd PCT/PTO 03 JAN 2006

<b>INFORMATION DISCLOSURE STATEMENT TRANSMITTAL</b>  To Commissioner For Patents Enclosed herewith is a Form PTO-1449, any required copies of documents listed thereon, and any concise explanation of their relevance is indicated below per 37 CFR 1.97.	Application Number	10/563483
	Filing Date	
	First Named Inventor	PONOMAREV YOURI
	Group Art Unit	2823
	Examiner Name	M. Estrada
	Atty. Docket Number	NL03 0833 US1

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number No.-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear
ME	1	US- 4 665 412	05/12/1987	OHKAWA TIHIRO	
ME	2	US- 4 695 857	09/22/1987	BABA TOSHIO	
ME	3	US- 5 055 887	10/08/1991	YAMAZAKI SHUNPEI	
ME	4	US- 4 908 678	03/13/1990	YAMAZAKI SHUNPEI	
		US-			
		US-			

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number (ciry <sup>3</sup> -no. <sup>4</sup> -kind <sup>5</sup> , if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of cited document	Pages, Columns Lines, Where Relevant Passages or Relevant Figures Appear

NON-PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in capital letters), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		
ME	1	KOJI Y ET AL: "THE FORMATION OF RESONANCE TUNNEL DIVICE BY GAMMA-AL203/SI . . . "; EXTENDED ABSTRACTS OF THE INTERNATIONAL CONFERENCE ON SOLID STATE DEVICES AND MATERIALS; JAPAN SOCIETY OF APPLIED PHYSICS; TOKYO JA; Vol. 2001; 26-September 2001; pages 588-589		
ME	2	LU Z H ET AL: "CRYSTALLINE Si/SiO 2 QUANTUM WELLS"; APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS; NEW YORK, US; Vol. 80, No. 2; 14 January 2002; pages 255-257		
ME	3	MEREU B ET AL: "FOWLER-NORDHEIM TUNNELING IN EPITAXIAL YTTRIUM OXIDE ON SILICON FOR HIGH-K GATE APPLICATIONS"; 2002 INTERNATIONAL SEMICONDUCTOR CONFERENCE; CAS 2002 PROCEEDINGS; IEEE PISCATAWAY; NJ USA; Vol. 2 8 Oct. 2002; pages 309-312		
ME	4	J. ALIEU ET AL: "MULTIPLE SiGe QUANTUM WELLS - NOVEL CHANNEL ARCHITECTURE FOR 0.2 CMOS"; PROCEEDINGS OF THE 29TH EUROPEAN SOLID-STATE DEVICE RESEARCH CONFERENCE; LEUVEN, BELGIUM; 13-15 SEP. 1999; P. 292-295		

Examiner Signature	Michelle Estrada	Date Considered	2/2/08
--------------------	------------------	-----------------	--------